PI Sheet



High Power Single Mode SemiNex Lasers 12xx to 19xx nm Custom Wavelengths Available

- ApplicationsOTDR
- LiDAR
- Free Space CommunicationsNetwork Test equipment

## Features

- High Output PowerHigh Dynamic Range

- High EfficiencyStandard Low Cost Package

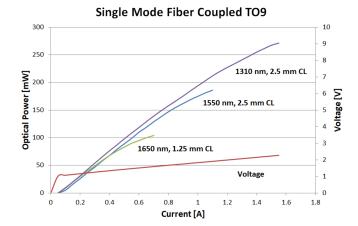


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DIODES

SemiNex delivers the highest available power at infrared wavelengths between 12xx and 19xx nm. When necessary wavelengths between 12xx and 19xx nm. When necessary we will further optimize the design of our InP laser chips to meet our customers' specific optical and electrical performance needs. Diodes, bars and packages are tested to meet customer and market performance demands. Typical results and packaging options are shown. Contact SemiNex for additional details or to discuss your specific requirements. requirements.





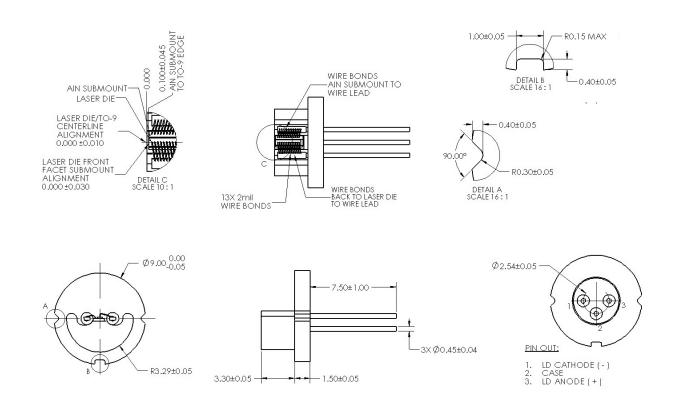






	Symbol	TO9F-106	Units
Optical			
Navelength	λ <sub>c</sub>	1660	nm (±20)
Dutput Power (CW)	P•	0.10	watts (±10%)
Chip Cavity Length	CL	2500	μm
Emitter Width	W	9	μm
Emitter Height	Н	0	μm
Spectral Width	δλ	10	nm 3dB
Slope Efficiency	η°	0.15	W/A
Fast Axis Div.*	Θ perp	8	deg FWHM
Slow Axis Div.	O_parallel	8	deg FWHM
Electrical			
Power Conversion Eff.	η	8	%
Operating Current	I <sub>op</sub>	0.6	A
Fhreshold Current	l <sub>th</sub>	0.07	A
Dperating Voltage	V <sub>op</sub>	2.1	V
Mechanical			
Neight		13.5	g
Operating Temp.**		-40 to 60	°C
Storage Temp.		-40 to 80	°C

Specified values are rated at a constant heat sink temperature of 20°C. \*\*Specified operating conditions are based on 20C heat sink temperature. High temperature operation will reduce performance and MTTF. Unless otherwise indicated all values are nominal. Uncapped TO9 specifications assume heatsinking underneath laser chip. Capped TO9 specifications assume heatsinking only on flat surface where pins extend.



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Date Created: Dec 1 2023 1:19PM UTC

DANGER SIBLE / INVISIBLE LASER RADIATI CLASS IIIb and IV LASER PRODUCTS product complex with 21CFR1040 as applicable appetrue is on the test station. Laser relations in this product is considered an acute hazard to the source area.

This product Laser apertu from this pro skin and eve